# N-Channel 60-V (D-S) MOSFET

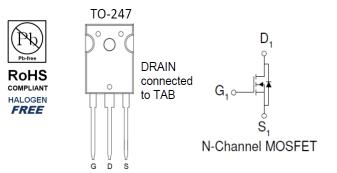
### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

## **Typical Applications:**

- Automotive Systems
- DC/DC Conversion Circuits
- Battery Powered Power Tools

PRODUCT SUMMARY				
VDS (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
60	8.5 @ V <sub>GS</sub> = 10V	110 <sup>a</sup>		
00	11 @ V <sub>GS</sub> = 4.5V	110		



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			60	V		
Gate-Source Voltage		V <sub>GS</sub>	±20	v		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>D</sub>	110 A			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	520	A		
Continuous Source Current (Diode Conduction) <sup>a</sup>	T <sub>C</sub> =25°C	ا <sub>s</sub>	110	А		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	PD	500	W		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{ extsf{ heta}JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	0.29	C/ VV		

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	$I_{GSS}$ $V_{DS} = 0 V, V_{GS} = \pm 20 V$				±100	nA	
Zoro Coto Voltogo Droin Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	°C 1(		10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	150			А	
Drain Course On Desistence a	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$			8.5	m0	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_{D} = 16 \text{ A}$			11	mΩ	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		63		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		0.85		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Qg	$V_{DS} = 30 \text{ V}, V_{GS} = 4.5 \text{ V},$		32		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{\rm DS} = 30$ V, $V_{\rm GS} = 4.3$ V, $I_{\rm D} = 20$ A		11			
Gate-Drain Charge	$Q_gd$	1 <u>0</u> – 20 A		9.6			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 30 \text{ V}, \text{ R}_{1} = 1.5 \Omega,$		11			
Rise Time	t <sub>r</sub>	$V_{\rm DS} = 30$ V, $N_{\rm L} = 1.3$ Ω, $I_{\rm D} = 20$ A,		10		200	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		111		ns	
Fall Time	t <sub>f</sub>	$v_{\text{GEN}} = 10 v, n_{\text{GEN}} - 0 \Omega$		31			
Input Capacitance	C <sub>iss</sub>			4107			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 Mhz		222		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			179			

#### Notes

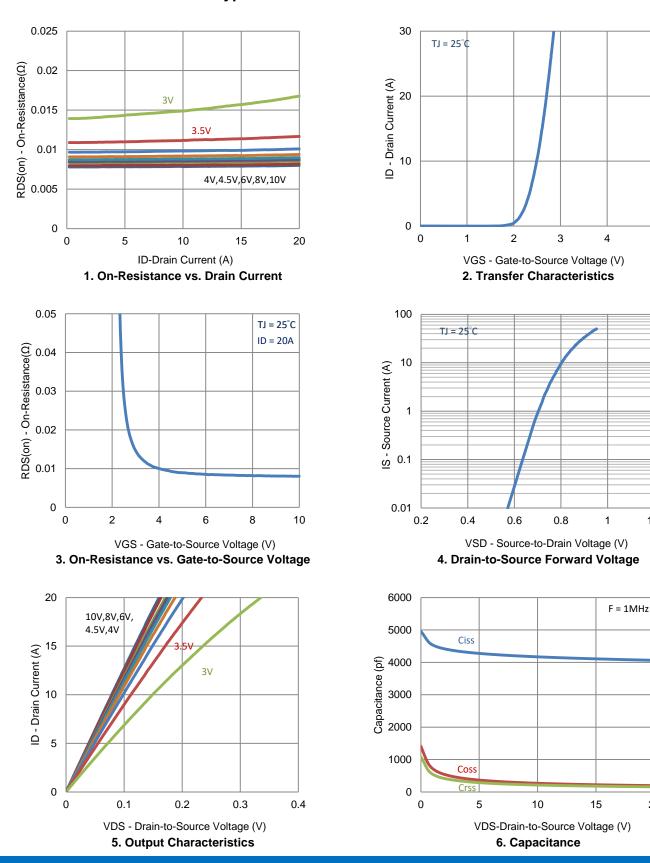
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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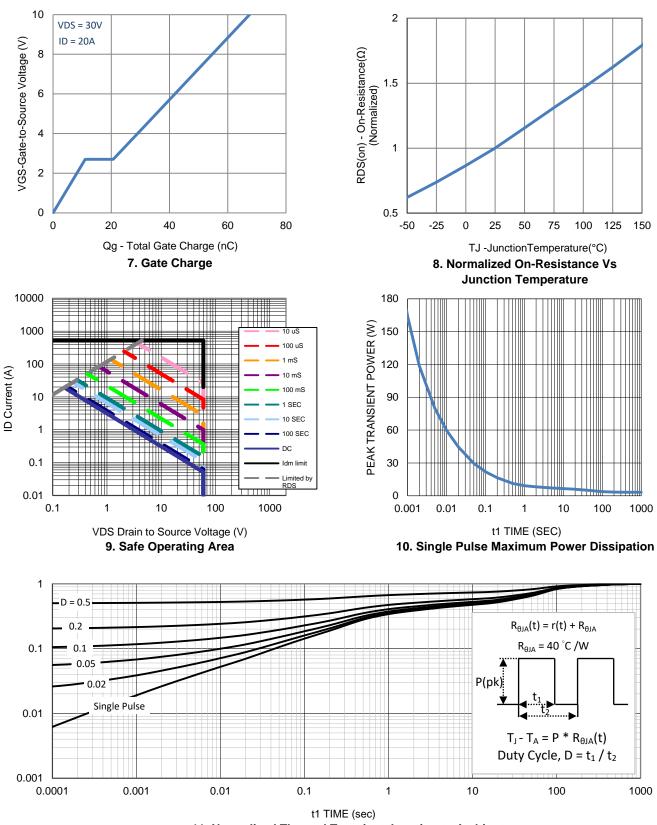
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1.2

20



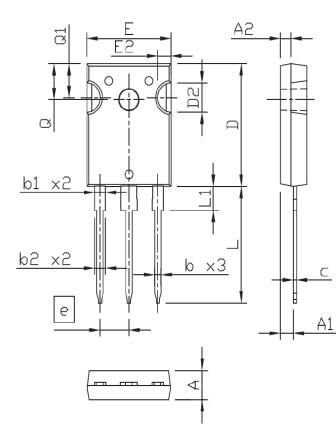
### **Typical Electrical Characteristics**

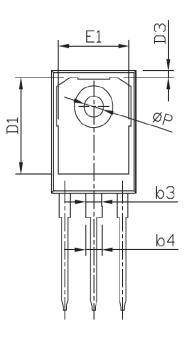


# **Typical Electrical Characteristics**

11. Normalized Thermal Transient Junction to Ambient

# Package Information





SYMBOLS	DIMENSIONS IN MILLIMETERS				
STMBULS	MIN	NDM	MAX		
A	4,90	5,00	5,10		
A1	2.32	2.42	2,52		
A2	1,90	2,00	2,10		
b	1.17	1.22	1.27		
b1	1,97	2,02	2,07		
b2	2.00	2.10	2.20		
b3	2,97	3.02	3,07		
b4	3.00	3.10 0.62	3.20		
С	0,59	0.62	0.66		
D	20,90	21,00	21,10		
D1	16.25	16.55	16.85		
D2		5,00 TYP			
D3	1.05	1.20	1.35		
e		<u>5.44 BSC</u>	2		
e E	15.70	15.80	15.90		
E1	13.06	13.26	13,46		
E2	2,50 TYP				
L	19.72	19.92	20.12		
L1			4,30		
Q	6.15 BSC				
Q1	5,60	5.80	6.00		
ØP	3.55	3.60	3.65		